

## ZXTP2041F

### SOT23 40 volt PNP silicon planar medium power transistor

#### Summary

$V_{(BR)CEO} > -40V$

$I_{c(cont)} = -1A$

$V_{ce(sat)} < -500mV @ -1A$



#### Complementary type

ZXTN2040F

#### Description

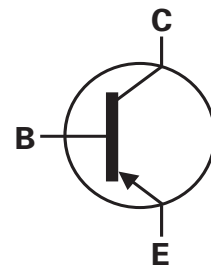
This transistor combines high gain, high current operation and low saturation voltage making it ideal for power MOSFET gate driving and low loss power switching.

#### Features

- Low saturation voltage for reduced power dissipation
- 1 to 2 amp high current capability
- Pb-free
- SOT23 package

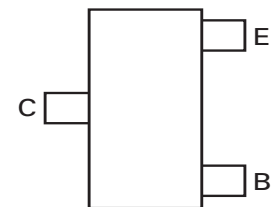
#### Applications

- Power MOSFET gate driving
- Low loss power switching



#### Ordering information

Device	Reel size	Tape width	Quantity per reel
ZXTP2041FTA	7"	8mm	3,000
ZXTP2041FTC	13"	8mm	10,000



Pinout - top view

#### Device marking

P41

# ZXTP2041F

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-Base voltage	$V_{CBO}$	-40	V
Collector-Emitter voltage	$V_{CEO}$	-40	V
Emitter-Base voltage	$V_{EBO}$	-5.0	V
Peak pulse current	$I_{CM}$	-2	A
Continuous collector current (*)	$I_C$	-1	A
Peak base current	$I_{BM}$	-1	A
Power dissipation @ $T_A=25^{\circ}C^{(*)}$	$P_D$	350	mW
Operating and storage temperature	$T_j; T_{stg}$	-55 to +150	$^{\circ}C$

### NOTES:

(\*) For a device surface mounted on a 15mm x 15mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

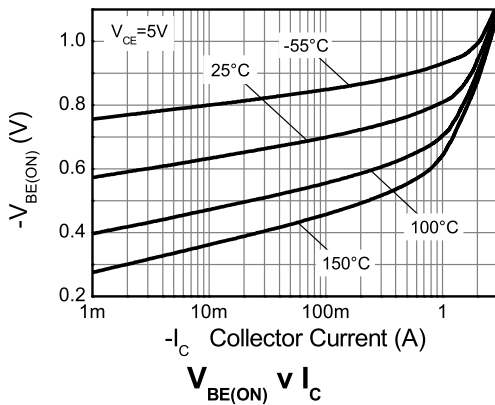
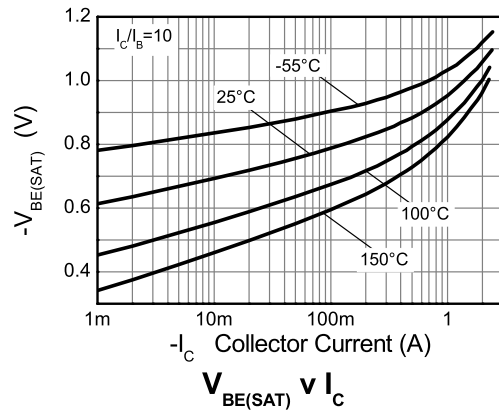
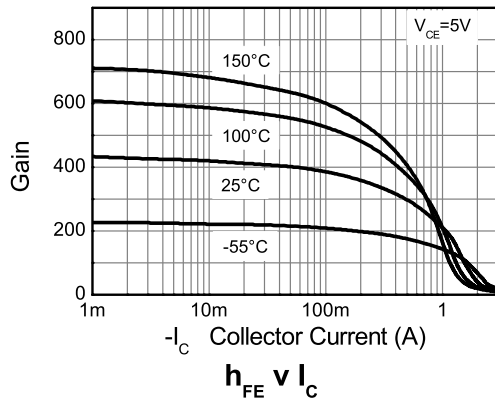
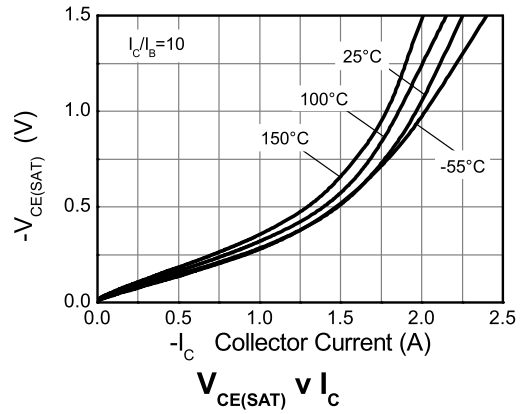
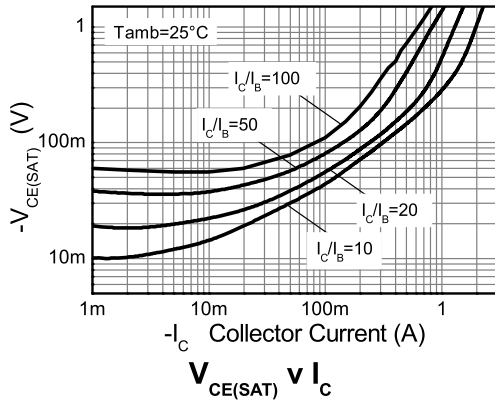
## Electrical characteristics (@T<sub>AMB</sub> = 25°C)

Parameter	Symbol	Min.	Max.	Unit	Conditions
Collector-Base breakdown voltage	V <sub>(BR)CBO</sub>	-40		V	I <sub>C</sub> =-100μA
Collector-Emitter breakdown voltage	V <sub>(BR)CEO</sub>	-40		V	I <sub>C</sub> =-10mA <sup>(*)</sup>
Emitter-Base breakdown voltage	V <sub>(BR)EBO</sub>	-5		V	I <sub>E</sub> =-100μA
Collector-Emitter cut-off current	I <sub>CEs</sub>		-100	nA	V <sub>CE</sub> =-30V
Collector-Base cut-off current	I <sub>CBO</sub>		-100	nA	V <sub>CB</sub> =-30V
Emitter-Base cut-off current	I <sub>EBO</sub>		-100	nA	V <sub>EB</sub> =-4V
Static forward current transfer ratio	h <sub>FE</sub>	300 300 250 160 30	800		I <sub>C</sub> =-1mA, V <sub>CE</sub> =-5V I <sub>C</sub> =-100mA, V <sub>CE</sub> =-5V <sup>(*)</sup> I <sub>C</sub> =-500mA, V <sub>CE</sub> =-5V <sup>(*)</sup> I <sub>C</sub> =-1A, V <sub>CE</sub> =-5V <sup>(*)</sup> I <sub>C</sub> =-2A, V <sub>CE</sub> =-5V <sup>(*)</sup>
Collector-Emitter saturation voltage	V <sub>CE(sat)</sub>		-0.2 -0.3 -0.5	V V V	I <sub>C</sub> =-100mA, I <sub>B</sub> =-1mA <sup>(*)</sup> I <sub>C</sub> =-500mA, I <sub>B</sub> =-20mA <sup>(*)</sup> I <sub>C</sub> =-1A, I <sub>B</sub> =-100mA <sup>(*)</sup>
Base-Emitter saturation voltage	V <sub>BE(sat)</sub>		-1.1	V	I <sub>C</sub> =-1A, I <sub>B</sub> =-50mA <sup>(*)</sup>
Base-Emitter turn-on voltage	V <sub>BE(on)</sub>		-1.0	V	I <sub>C</sub> =-1A, V <sub>CE</sub> =-5V <sup>(*)</sup>
Transition frequency	f <sub>T</sub>	150			I <sub>C</sub> =-50mA, V <sub>CE</sub> =-10V f=100MHz
Output capacitance	C <sub>obo</sub>		10	pF	V <sub>CB</sub> =-10V, f=1MHz

### NOTES:

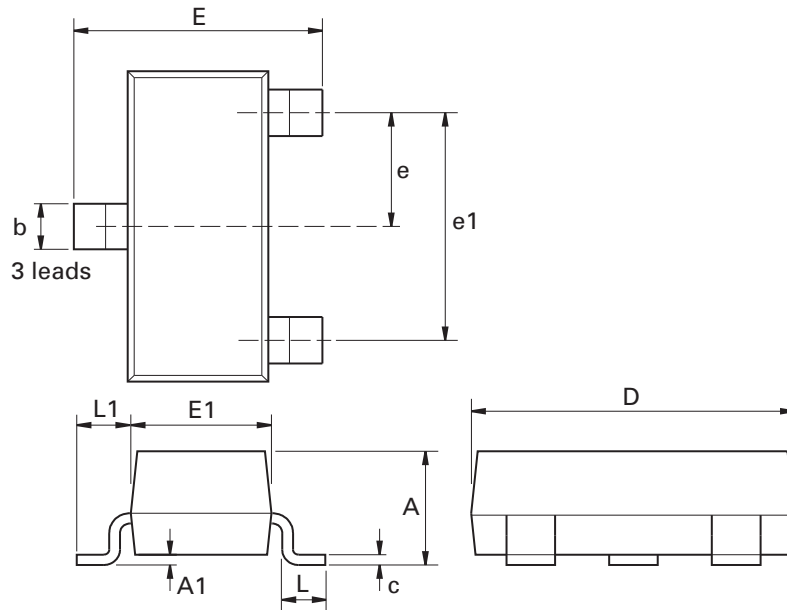
(\*) Measured under pulsed conditions. Pulse width=300 μs. Duty cycle ≤2%  
Spice parameter data is available upon request for this device

## PNP electrical characteristics



# ZXTP2041F

## Packaging details - SOT23



## Package dimensions

Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	-	1.12	-	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	E	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
c	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
e	0.95 NOM		0.037 NOM		-	-	-	-	-

NOTE: Controlling dimensions in millimetres. Approximate dimensions are provided in inches..

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